### DATASHEET

### Description

The 9DBU0431 is a member of IDT's 1.5V Ultra-Low-Power (ULP) PCIe family. The device has 4 output enables for clock management, and 3 selectable SMBus addresses.

### **Recommended Application**

1.5V PCIe Gen1-2-3 Zero-Delay/Fan-out Buffer (ZDB/FOB)

### **Output Features**

• 4 – 1-167MHz Low-Power (LP) HCSL DIF pairs

### **Key Specifications**

- DIF cycle-to-cycle jitter <50ps
- DIF output-to-output skew <50ps
- DIF phase jitter is PCIe Gen1-2-3 compliant
- DIF bypass mode additive phase jitter is <300fs rms for PCIe Gen3
- DIF bypass mode additive phase jitter <350fs rms for 12k-20MHz

### Features/Benefits

- LP-HCSL outputs; save 8 resistors compared to standard HCSL outputs
- 45mW typical power consumption in PLL mode; eliminates thermal concerns
- Spread Spectrum (SS) compatible; allows SS for EMI reduction
- OE# pins; support DIF power management
- HCSL-compatible differential input; can be driven by common clock sources
- SMBus-selectable features; optimize signal integrity to application
  - slew rate for each output
  - differential output amplitude
- Pin/software selectable PLL bandwidth and PLL Bypass; optimize PLL to application
- Outputs blocked until PLL is locked; clean system start-up
- Device contains default configuration; SMBus interface not required for device control
- 3.3V tolerant SMBus interface works with legacy controllers
- Three selectable SMBus addresses; multiple devices can easily share an SMBus segment
- Space saving 32-pin 5x5mm VFQFPN; minimal board space



### **Block Diagram**

### **Pin Configuration**



#### 32-pin VFQFPN, 5x5 mm, 0.5mm pitch

 ^ prefix indicates internal 120KOhm pull up resistor
 ^v prefix indicates internal 120KOhm pull up AND pull down resistor (biased to VDD/2)
 v prefix indicates internal 120KOhm pull down resistor

#### **SMBus Address Selection Table**

	SADR	Address	+ Read/Write bit
State of SADR on first application of	0	1101011	Х
CKPWRGD PD#	М	1101100	Х
CKPWRGD_PD#	1	1101101	x

#### **Power Management Table**

CKPWRGD PD#	CLK IN	SMBus OEx# Pin		DIF	PLL	
		OEx bit		True O/P Comp. O/P		FLL
0	Х	X	X	Low	Low	Off
1	Running	0	Х	Low	Low	On <sup>1</sup>
1	Running	1	0	Running	Running	On <sup>1</sup>
1	Running	1	1	Low	Low	On <sup>1</sup>

1. If Bypass mode is selected, the PLL will be off, and outputs will be running.

#### **Power Connections**

Pin Numb	Pin Number				
VDD	GND	Description			
4	7	Input receiver analog			
9	8	Digital Power			
16, 25	15,20,26,30	DIF outputs			
21	20	PLL Analog			

Note: epad on this device is not electrically connected to the die. It should be connected to ground for best thermal performance.

### PLL Operating Mode

HiBW_BypM_LoBW#	MODE	Byte1 [7:6] Readback	Byte1 [4:3] Control
0	PLL Lo BW	00	00
М	Bypass	01	01
1	PLL Hi BW	11	11

# **Pin Descriptions**

Pin#	Pin Name	Туре	Pin Description
-			Trilevel input to select High BW, Bypass or Low BW mode.
1	^vHIBW_BYPM_LOBW#	LATCHED IN	See PLL Operating Mode Table for Details.
2	FB_DNC	DNC	True clock of differential feedback. The feedback output and feedback input are
2		DINC	connected internally on this pin. Do not connect anything to this pin.
3	FB_DNC#	DNC	Complement clock of differential feedback. The feedback output and feedback
5		DINC	input are connected internally on this pin. Do not connect anything to this pin.
4	VDDR1.5	PWR	1.5V power for differential input clock (receiver). This VDD should be treated as
-			an Analog power rail and filtered appropriately.
5	CLK_IN	IN	True Input for differential reference clock.
6	CLK_IN#	IN	Complementary Input for differential reference clock.
7	GNDR	GND	Analog Ground pin for the differential input (receiver)
8	GNDDIG	GND	Ground pin for digital circuitry
9	VDDDIG1.5	PWR	1.5V digital power (dirty power)
10	SCLK_3.3	IN	Clock pin of SMBus circuitry, 3.3V tolerant.
11	SDATA_3.3	I/O	Data pin for SMBus circuitry, 3.3V tolerant.
12	vOE0#	IN	Active low input for enabling DIF pair 0. This pin has an internal pull-down.
			1 =disable outputs, 0 = enable outputs
13	DIF0	OUT	Differential true clock output
14	DIF0#	OUT	Differential Complementary clock output
15	GND	GND	Ground pin.
16	VDDO1.5	PWR	Power supply for outputs, nominally 1.5V.
17	vOE1#	IN	Active low input for enabling DIF pair 1. This pin has an internal pull-down.
			1 =disable outputs, 0 = enable outputs
18	DIF1	OUT	Differential true clock output
19	DIF1#	OUT	Differential Complementary clock output
20	GNDA	GND	Ground pin for the PLL core.
21	VDDA1.5	PWR	1.5V power for the PLL core.
22	DIF2		Differential true clock output
23	DIF2#	OUT	Differential Complementary clock output
24	vOE2#	IN	Active low input for enabling DIF pair 2. This pin has an internal pull-down.
05			1 =disable outputs, 0 = enable outputs
25	VDDO1.5 GND	PWR	Power supply for outputs, nominally 1.5V.
26		GND	Ground pin.
27	DIF3		Differential true clock output
28	DIF3#	OUT	Differential Complementary clock output Active low input for enabling DIF pair 3. This pin has an internal pull-down.
29	vOE3#	IN	
30	GND	GND	1 =disable outputs, 0 = enable outputs Ground pin.
- 30			Input notifies device to sample latched inputs and start up on first high assertion.
31	^CKPWRGD_PD#	IN	Low enters Power Down Mode, subsequent high assertions exit Power Down
51			Mode. This pin has internal pull-up resistor.
32	^SADR_tri	LATCHED IN	Tri-level latch to select SMBus Address. See SMBus Address Selection Table.
33	EPAD	GND	Connect ePAD to ground.

### **Test Loads**



#### Alternate Differential Output Terminations

Rs	Zo	Units
33	100	Ohms
27	85	Onins

# **Driving LVDS**



#### Driving LVDS inputs

	, ,		
	Receiver has Receiver does not		
Component	termination	have termination	Note
R7a, R7b	10K ohm	140 ohm	
R8a, R8b	5.6K ohm	75 ohm	
Cc	0.1 uF	0.1 uF	
Vcm	1.2 volts	1.2 volts	

## **Absolute Maximum Ratings**

Stresses above the ratings listed below can cause permanent damage to the 9DBU0431. These ratings, which are standard values for IDT commercially rated parts, are stress ratings only. Functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods can affect product reliability. Electrical parameters are guaranteed only over the recommended operating temperature range.

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	МАХ	UNITS	NOTES
Supply Voltage	VDDx		-0.5		2	V	1,2
Input Voltage	V <sub>IN</sub>		-0.5		V <sub>DD</sub> +0.5	V	1,3
Input High Voltage, SMBus	VIHSMB	SMBus clock and data pins			3.3	V	1
Storage Temperature	Ts		-65		150	°C	1
Junction Temperature	Tj				125	°C	1
Input ESD protection	ESD prot	Human Body Model	2000			V	1

<sup>1</sup>Guaranteed by design and characterization, not 100% tested in production.

<sup>2</sup> Operation under these conditions is neither implied nor guaranteed.

<sup>3</sup> Not to exceed 2.0V.

### **Electrical Characteristics–Clock Input Parameters**

TA = T<sub>AMB</sub>, Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

		,					
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Input Common Mode Voltage - DIF_IN	V <sub>COM</sub>	Common Mode Input Voltage	200		725	mV	1
Input Swing - DIF_IN	V <sub>SWING</sub>	Differential value	300		1450	mV	1
Input Slew Rate - DIF_IN	dv/dt	Measured differentially	0.4		8	V/ns	1,2
Input Leakage Current	I <sub>IN</sub>	$V_{IN} = V_{DD}, V_{IN} = GND$	-5		5	uA	
Input Duty Cycle	d <sub>tin</sub>	Measurement from differential wavefrom	45	50	55	%	1
Input Jitter - Cycle to Cycle	J <sub>DIFIn</sub>	Differential Measurement	0		150	ps	1

<sup>1</sup> Guaranteed by design and characterization, not 100% tested in production.

<sup>2</sup> Slew rate measured through +/-75mV window centered around differential zero

# Electrical Characteristics–Input/Supply/Common Parameters–Normal Operating Conditions

TA = T<sub>AMB</sub>; Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Supply Voltage	VDDx	Supply voltage for core and analog	1.425	1.5	1.575	V	
Ambient Operating	T <sub>AMB</sub>	Commmercial range	0	25	70	°C	1
Temperature	I AMB	Industrial range	-40	25	85	°C	1
Input High Voltage	V <sub>IH</sub>	Single-ended inputs, except SMBus	$0.75 V_{DD}$		$V_{DD} + 0.3$	V	
Input Mid Voltage	V <sub>IM</sub>	Single-ended tri-level inputs ('_tri' suffix)	$0.4 V_{DD}$		0.6 V <sub>DD</sub>	V	
Input Low Voltage	V <sub>IL</sub>	Single-ended inputs, except SMBus	-0.3		$0.25 V_{DD}$	V	
	IN	Single-ended inputs, $V_{IN} = GND$ , $V_{IN} = VDD$	-5		5	uA	
Input Current	I <sub>INP</sub>	Single-ended inputs V <sub>IN</sub> = 0 V; Inputs with internal pull-up resistors V <sub>IN</sub> = VDD; Inputs with internal pull-down resistors	-200		200	uA	
Input Frequency	F <sub>ibyp</sub>	Bypass mode	1		167	MHz	2
Input Frequency	F <sub>ipll</sub>	100MHz PLL mode	20	100.00	110	MHz	2
Pin Inductance	L <sub>pin</sub>				7	nH	1
	C <sub>IN</sub>	Logic Inputs, except DIF_IN	1.5		5	pF	1
Capacitance	C <sub>INDIF_IN</sub>	DIF_IN differential clock inputs	1.5		2.7	рF	1,5
	C <sub>OUT</sub>	Output pin capacitance			6	рF	1
Clk Stabilization	T <sub>STAB</sub>	From V <sub>DD</sub> Power-Up and after input clock stabilization or de-assertion of PD# to 1st clock			1	ms	1,2
Input SS Modulation Frequency PCIe	f <sub>MODINPCIe</sub>	Allowable Frequency for PCIe Applications (Triangular Modulation)	30		33	kHz	
Input SS Modulation Frequency non-PCIe	f <sub>MODIN</sub>	Allowable Frequency for non-PCIe Applications (Triangular Modulation)	0		66	kHz	
OE# Latency	t <sub>LATOE#</sub>	DIF start after OE# assertion DIF stop after OE# deassertion	1		3	clocks	1,3
Tdrive_PD#	t <sub>DRVPD</sub>	DIF output enable after PD# de-assertion			300	us	1,3
Tfall	t <sub>F</sub>	Fall time of single-ended control inputs			5	ns	2
Trise	t <sub>R</sub>	Rise time of single-ended control inputs			5	ns	2
SMBus Input Low Voltage	VILSMB				0.6	V	
SMBus Input High Voltage	VIHSMB	$V_{DDSMB}$ = 3.3V, see note 4 for $V_{DDSMB}$ < 3.3V	2.1		3.3	V	4
SMBus Output Low Voltage	V <sub>OLSMB</sub>	@ I <sub>PULLUP</sub>			0.4	V	
SMBus Sink Current	I <sub>PULLUP</sub>	@ V <sub>OL</sub>	4			mA	
Nominal Bus Voltage	V <sub>DDSMB</sub>	Bus Voltage	1.425		3.3	V	
SCLK/SDATA Rise Time	t <sub>RSMB</sub>	(Max VIL - 0.15) to (Min VIH + 0.15)			1000	ns	1
SCLK/SDATA Fall Time	t <sub>FSMB</sub>	(Min VIH + 0.15) to (Max VIL - 0.15)			300	ns	1
SMBus Operating Frequency	f <sub>MAXSMB</sub>	Maximum SMBus operating frequency			400	kHz	6

<sup>1</sup>Guaranteed by design and characterization, not 100% tested in production.

 $^2\mbox{Control}$  input must be monotonic from 20% to 80% of input swing.

 $^{3}$ Time from deassertion until outputs are >200 mV

 $^4$  For V\_{DDSMB} < 3.3V, V\_{IHSMB} >= 0.8 x V\_{DDSMB}

<sup>5</sup>DIF\_IN input

<sup>6</sup>The differential input clock must be running for the SMBus to be active

### **Electrical Characteristics–DIF Low-Power HCSL Outputs**

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Slew rate	dV/dt	Scope averaging on, fast setting	1.4	2.2	3.5	V/ns	1,2,3
Slew late	dV/dt	Scope averaging on, slow setting	0.9	1.7	2.5	V/ns	1,2,3
Slew rate matching	∆dV/dt	Slew rate matching, Scope averaging on		2.7	20	%	1,2,4
Voltage High	V <sub>HIGH</sub>	Statistical measurement on single-ended signal	630	735	850	mV	7
Voltage Low	V <sub>LOW</sub>	using oscilloscope math function. (Scope averaging on)		-16	150		7
Max Voltage	Vmax	Measurement on single ended signal using		779	1150	mV	7
Min Voltage	Vmin	absolute value. (Scope averaging off)	-300	-45			7
Vswing	Vswing	Scope averaging off	300	1503		mV	1,2
Crossing Voltage (abs)	Vcross_abs	Scope averaging off	250	405	550	mV	1,5
Crossing Voltage (var)	∆-Vcross	Scope averaging off		12	140	mV	1,6

TA = T<sub>AMB</sub>; Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

<sup>1</sup>Guaranteed by design and characterization, not 100% tested in production.

<sup>2</sup> Measured from differential waveform

<sup>3</sup> Slew rate is measured through the Vswing voltage range centered around differential 0V. This results in a +/-150mV window around differential 0V.

<sup>4</sup> Matching applies to rising edge rate for Clock and falling edge rate for Clock#. It is measured using a +/-75mV window centered on the average cross point where Clock rising meets Clock# falling. The median cross point is used to calculate the voltage thresholds the oscilloscope is to use for the edge rate calculations.

<sup>5</sup> Vcross is defined as voltage where Clock = Clock# measured on a component test board and only applies to the differential rising edge (i.e. Clock rising and Clock# falling).

<sup>6</sup> The total variation of all Vcross measurements in any particular system. Note that this is a subset of Vcross\_min/max (Vcross absolute) allowed. The intent is to limit Vcross induced modulation by setting  $\Delta$ -Vcross to be smaller than Vcross absolute.

<sup>7</sup> At default SMBus settings.

### **Electrical Characteristics–Current Consumption**

TA = T<sub>AMB</sub>; Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Operating Supply Current	I <sub>DDR</sub>	VDDR @100MHz		4	6	mA	1
	DDDIG	VDDIG, All outputs @100MHz		0.125	0.25	mA	1
	I <sub>DDAO</sub>	VDDA+VDDO, PLL Mode, All outputs @100MHz		24	30	mA	1
	DDRPD	VDDR, CKPWRGD_PD# = 0		0.1	0.3	mA	1,2,3
Powerdown Current		VDDDIG, CKPWRGD_PD# = 0		0.1	0.2	mA	1,2
	DDAOPD	VDDA+VDDO, CKPWRGD_PD# = 0		0.5	1	mA	1,2

<sup>1</sup> Guaranteed by design and characterization, not 100% tested in production.

<sup>2</sup> Input clock stopped.

 $^3$  In bypass mode, the PLL is off and IDDAO is ~50% of this value.

### Electrical Characteristics–Output Duty Cycle, Jitter, Skew and PLL Characteristics

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
PLL Bandwidth	BW	-3dB point in High BW Mode (100MHz)	2.2	3.6	4.8	MHz	1,5
PLL Bandwidth	DVV	-3dB point in Low BW Mode (100MHz)11.62.5MHzPeak Pass band Gain (100MHz)1.32.5dBMeasured differentially, PLL Mode4550.255%	1,5				
PLL Jitter Peaking	t <sub>JPEAK</sub>	Peak Pass band Gain (100MHz)	Pass band Gain (100MHz)		2.5	dB	1
Duty Cycle	t <sub>DC</sub>	Measured differentially, PLL Mode	45	50.2	55	%	1
Duty Cycle Distortion	t <sub>DCD</sub>	Measured differentially, Bypass Mode @100MHz	-1	-0.6	0	%	1,3
Ckow Input to Output	t <sub>pdBYP</sub>	Bypass Mode, V <sub>T</sub> = 50%	3400	4300	5200	ps	1
Skew, Input to Output	t <sub>pdPLL</sub>	PLL Mode V <sub>T</sub> = 50%	0	50	150	ps	1,4
Skew, Output to Output	t <sub>sk3</sub>	V <sub>T</sub> = 50%		37	50	ps	1,4
Jitter, Cycle to cycle	+	PLL mode		24	50	ps	1,2
Jitter, Cycle to Cycle	τ <sub>jcyc-cyc</sub>	Additive Jitter in Bypass Mode		0.1	5	ps	1,2

TA = T<sub>AMB</sub>; Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

<sup>1</sup> Guaranteed by design and characterization, not 100% tested in production.

<sup>2</sup> Measured from differential waveform

<sup>3</sup> Duty cycle distortion is the difference in duty cycle between the output and the input clock when the device is operated in bypass mode.

<sup>4</sup> All outputs at default slew rate

<sup>5</sup> The MIN/TYP/MAX values of each BW setting track each other, i.e., Low BW MAX will never occur with Hi BW MIN.

### **Electrical Characteristics–Phase Jitter Parameters**

 $TA = T_{AMB}$ ; Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

						INDUSTRY		
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	LIMIT	UNITS	Notes
	t <sub>jphPCleG1</sub>	PCIe Gen 1		30	58	86	ps (p-p)	1,2,3,5
Phase Jitter, PLL Mode	+	PCIe Gen 2 Lo Band 10kHz < f < 1.5MHz		0.9	1.4	3	ps (rms)	1,2,3,5
	t <sub>jphPCleG2</sub>	PCIe Gen 2 High Band 1.5MHz < f < Nyquist (50MHz)		2.1	2.6	3.1	ps (rms)	1,2,3,5
	t <sub>jphPCleG3</sub>	PCIe Gen 3 Common Clock Architecture (PLL BW of 2-4 or 2-5MHz, CDR = 10MHz)		0.5	0.6	1	ps (rms)	1,2,3,5
	t <sub>jphPCleG3SRn</sub> S	PCIe Gen 3 Separate Reference No Spread (SRnS) (PLL BW of 2-4 or 2-5MHz, CDR = 10MHz)		0.5	0.6	0.7	ps (rms)	1,2,3,5
	t <sub>jphPCleG1</sub>	PCIe Gen 1		0.1	5	N/A	ps (p-p)	1,2,3,5
	+	PCIe Gen 2 Lo Band 10kHz < f < 1.5MHz		0.1	0.5	N/A	ps (rms)	1,2,3,4, 5
	t <sub>jphPCleG2</sub>	PCIe Gen 2 High Band 1.5MHz < f < Nyquist (50MHz)		0.1	0.3	N/A	ps (rms)	1,2,3,4
Additive Phase Jitter, Bypass Mode	t <sub>jphPCleG3</sub>	PCIe Gen 3 (PLL BW of 2-4 or 2-5MHz, CDR = 10MHz)		0.2	0.3	N/A	ps (rms)	1,2,3,4
Dypass would	t <sub>jph125M0</sub>	125MHz, 1.5MHz to 10MHz, -20dB/decade rollover < 1.5MHz, -40db/decade rolloff > 10MHz		200	300	N/A	fs (rms)	1,6
	t <sub>jph125M1</sub>	125MHz, 12KHz to 20MHz, -20dB/decade rollover < 1.5MHz, -40db/decade rolloff > 10MHz		313	350	N/A	fs (rms)	1,6

<sup>1</sup>Guaranteed by design and characterization, not 100% tested in production.

<sup>2</sup> See http://www.pcisig.com for complete specs

<sup>4</sup> For RMS figures, additive jitter is calculated by solving the following equation: Additive jitter = SQRT[(total jitter)^2 - (input jitter)^2]

<sup>5</sup> Driven by 9FGU0831 or equivalent

<sup>6</sup> Rohde&Schartz SMA100

<sup>&</sup>lt;sup>3</sup> Sample size of at least 100K cycles. This figures extrapolates to 108ps pk-pk @ 1M cycles for a BER of 1-12.



### Additive Phase Jitter Plot: 125M (12kHz to 20MHz)

### **General SMBus Serial Interface Information**

#### How to Write

- Controller (host) sends a start bit
- Controller (host) sends the write address
- IDT clock will acknowledge
- Controller (host) sends the beginning byte location = N
- IDT clock will **acknowledge**
- Controller (host) sends the byte count = X
- IDT clock will acknowledge
- Controller (host) starts sending Byte N through Byte N+X-1
- IDT clock will acknowledge each byte one at a time
- Controller (host) sends a Stop bit

	Index BI	ock	Write Operation
Controll	er (Host)		IDT (Slave/Receiver)
Т	starT bit		
Slave A	Address		
WR	WRite		
			ACK
Beginning	g Byte = N		
			ACK
Data Byte	Count = X		
			ACK
Beginnin	ng Byte N		
			ACK
0		×	
0		X Byte	0
0		e	0
			0
Byte N	+ X - 1		
			ACK
Р	stoP bit		

### Note: SMBus Address is Latched on SADR pin.

#### How to Read

- Controller (host) will send a start bit
- Controller (host) sends the write address
- IDT clock will acknowledge
- Controller (host) sends the beginning byte location = N
- IDT clock will acknowledge
- Controller (host) will send a separate start bit
- Controller (host) sends the read address
- IDT clock will acknowledge
- IDT clock will send the data byte count = X
- IDT clock sends Byte N+X-1
- IDT clock sends Byte 0 through Byte X (if X<sub>(H)</sub> was written to Byte 8)
- Controller (host) will need to acknowledge each byte
- Controller (host) will send a not acknowledge bit
- Controller (host) will send a stop bit

	Index Block F	Read O	peration
Co	ntroller (Host)		IDT (Slave/Receiver)
Т	starT bit		
s	lave Address		
WR	WRite		
			ACK
Beg	inning Byte = N		
			ACK
RT	Repeat starT		
S	lave Address		
RD	ReaD		
			ACK
			Data Byte Count=X
	ACK		
			Beginning Byte N
	ACK		
		e	0
	0	X Byte	0
	0	×	0
	0	1	
			Byte N + X - 1
Ν	Not acknowledge		
Р	stoP bit		

Byte 0	Name	Control Function Type		0	1	Default		
Bit 7		Reserved						
Bit 6	DIF OE3	Output Enable	Output Enable RW Low/Low Enabled			1		
Bit 5	DIF OE2	Output Enable	Output Enable RW Low/Low Enabled					
Bit 4	Reserved							
Bit 3	DIF OE1	Output Enable	RW	Low/Low	Enabled	1		
Bit 2		Reserved				1		
Bit 1	DIF OE0	Output Enable	RW	Low/Low	Enabled	1		
Bit 0	Reserved							

#### SMBus Table: Output Enable Register <sup>1</sup>

1. A low on these bits will overide the OE# pin and force the differential output Low/Low

#### SMBus Table: PLL Operating Mode and Output Amplitude Control Register

Byte 1	Name	Control Function	Туре	0	1	Default
Bit 7	PLLMODERB1	PLL Mode Readback Bit 1	R	See PLL Operating Mode Table		Latch
Bit 6	PLLMODERB0	PLL Mode Readback Bit 0	R		Latch	
Bit 5	PLLMODE_SWCNTRL	Enable SW control of PLL Mode	RW	Values in B1[7:6] set PLL Mode		
Bit 4	PLLMODE1	PLL Mode Control Bit 1	RW <sup>1</sup>	See PLL Operating Mode Table		0
Bit 3	PLLMODE0	PLL Mode Control Bit 0	RW <sup>1</sup>	See FLL Operat	ing would rapie	0
Bit 2		Reserved				1
Bit 1	AMPLITUDE 1	Controls Output Amplitude	RW	00 = 0.55V	01 = 0.65V	1
Bit 0	AMPLITUDE 0	Controis Output Amplitude	RW	10= 0.75V	11 = 0.85V	0

1. B1[5] must be set to a 1 for these bits to have any effect on the part.

#### SMBus Table: DIF Slew Rate Control Register

Byte 2	Name	Control Function Type 0 1		Default		
Bit 7		Reserved				1
Bit 6	SLEWRATESEL DIF3	Slew Rate Selection	Slew Rate Selection RW Slow Setting Fast Setting		1	
Bit 5	SLEWRATESEL DIF2	Slew Rate Selection	Slew Rate Selection RW Slow Setting Fast Setting		1	
Bit 4	Reserved					
Bit 3	SLEWRATESEL DIF1	Slew Rate Selection	RW	Slow Setting	Fast Setting	1
Bit 2		Reserved				1
Bit 1	SLEWRATESEL DIF0	Slew Rate Selection	RW	Slow Setting	Fast Setting	1
Bit 0		Reserved				1

#### SMBus Table: FB Slew Rate Control Register

Byte 3	Name	Control Function	Туре	0	1	Default	
Bit 7	Reserved						
Bit 6		Reserved					
Bit 5		Reserved				0	
Bit 4	Reserved						
Bit 3		Reserved				0	
Bit 2		Reserved				1	
Bit 1	Reserved						
Bit 0	SLEWRATESEL FB	Adjust Slew Rate of FB	RW	Slow Setting	Fast Setting	1	

1. B3[5] must be set to a 1 for these bits to have any effect on the part.

#### Byte 4 is Reserved and reads back 'hFF

Byte 5	Name	Control Function	Туре	0	1	Default
Bit 7	RID3		R			0
Bit 6	RID2	Revision ID	R	A rev =	- 0000	0
Bit 5	RID1		R	A lev -	0	
Bit 4	RID0		R		0	
Bit 3	VID3		R			0
Bit 2	VID2	VENDOR ID	R	0001	0001 = IDT	
Bit 1	VID1	VENDORID	R	0001 – 101		0
Bit 0	VID0		R			1

#### SMBus Table: Revision and Vendor ID Register

#### SMBus Table: Device Type/Device ID

Byte 6	Name	Control Function	Туре	0	1	Default
Bit 7	Device Type1	Device Type	R	00 = FGx,	01 = DBx,	0
Bit 6	Device Type0	Device Type	R	10 = DMx, 1	1	
Bit 5	Device ID5		R			0
Bit 4	Device ID4		R		0	
Bit 3	Device ID3	Device ID	R	000100 bina	000100 binary or 04 hex	
Bit 2	Device ID2	Device ID	R			1
Bit 1	Device ID1	]	R			0
Bit 0	Device ID0		R			0

### SMBus Table: Byte Count Register

Byte 7	Name	Control Function	Туре	0	1	Default	
Bit 7	Reserved						
Bit 6		Reserved					
Bit 5	Reserved						
Bit 4	BC4		RW			0	
Bit 3	BC3		RW	Writing to this regist	1		
Bit 2	BC2	Byte Count Programming	RW	many bytes will be r	ead back, default is	0	
Bit 1	BC1		RW	= 8 b	ytes.	0	
Bit 0	BC0		RW			0	

### **Marking Diagrams**



Notes:

- 1. "LOT" is the lot sequence number.
- 2. "COO" denotes country of origin.
- 3. YYWW is the last two digits of the year and week that the part was assembled.
- 4. Line 2: truncated part number
- 5. "L" denotes RoHS compliant package.
- 6. "I" denotes industrial temperature range device.

### **Thermal Characteristics**

PARAMETER	SYMBOL	CONDITIONS	PKG	TYP VALUE	UNITS	NOTES
	θ <sub>JC</sub>	Junction to Case		42	°C/W	1
	$\theta_{Jb}$	Junction to Base	2.4		°C/W	1
Thermal Resistance	$\theta_{JA0}$	Junction to Air, still air	NLG32 39	°C/W	1	
	$\theta_{JA1}$	Junction to Air, 1 m/s air flow	NLG32	33	°C/W	1
	$\theta_{JA3}$	Junction to Air, 3 m/s air flow	28		°C/W	1
	$\theta_{JA5}$	Junction to Air, 5 m/s air flow		27	∘C/W	1

<sup>1</sup>ePad soldered to board

### Package Outline and Package Dimensions (NLG32) – use EPAD Option P1



# **Ordering Information**

Part / Order Number	Shipping Packaging	Package	Temperature
9DBU0431AKLF	Trays	32-pin VFQFPN	0 to +70° C
9DBU0431AKLFT	Tape and Reel	32-pin VFQFPN	0 to +70° C
9DBU0431AKILF	Trays	32-pin VFQFPN	-40 to +85° C
9DBU0431AKILFT	Tape and Reel	32-pin VFQFPN	-40 to +85° C

"LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant. "A" is the device revision designator (will not correlate with the datasheet revision).

# **Revision History**

Rev.	Initiator	Issue Date	Description	Page #
А	RDW	7/15/2014	<ol> <li>Updated electrical tables with char data.</li> <li>Added an additive phase jitter plot.</li> <li>Added 12kHz to 20MHz additive phase jitter spec.</li> <li>Updated Amplitude control bit descriptions in Byte 1.</li> </ol>	
В	RDW	9/19/2014	Updated SMBus Input High/Low parameters conditions, MAX values, and footnotes.	6
с	RDW	4/22/2015	<ol> <li>Updated pin out and pin descriptions to show ePad on package connected to ground.</li> <li>Updated front page text to standard format for these devices. Added explicit bullet indicated Spread Spectrum compatibility.</li> <li>Updated Clock Input Parameters table to be consistent with PCIe Vswing parameter.</li> <li>Minor updates to front page text for family consistency.</li> <li>Add note about epad to Power Connections table.</li> </ol>	

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